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				First Named Inventor	Munehiro TADA
				Art Unit	Not Yet Assigned
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Sheet	1	of 1		Attorney Docket Number	Q91732

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Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶		
		Tada, M., et al. "BARRIER-METAL-FREE (BMF), Cu DUAL-DAMASCENE INTERCONNECTS WITH Cu-epi-CONTACTS BURIED IN ANTI-DIFFUSIVE, LOW-k ORGANIC FILM," 2001 Symposium on VLSI Technology, June 12, 2001, pages 13-14.			
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